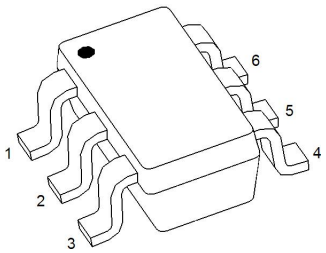
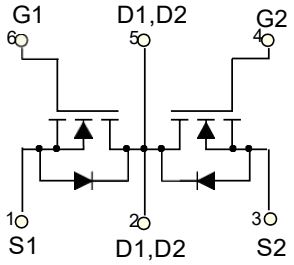
$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
20V	27mΩ@4.5V	5A
	32mΩ@2.5V	

SOT-23-6L



Schematic diagram



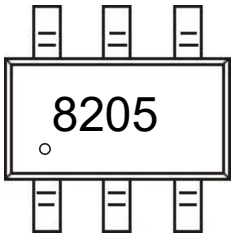
Feature

- Trench Technology Power MOSFET
- Low $R_{DS(ON)}$
- Low Gate Charge
- Low Gate Resistance

Application

- Power Switching Application

MARKING:



ABSOLUTE MAXIMUM RATINGS (T_A = 25℃ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain - Source Voltage		V_{DS}	20	V
Gate - Source Voltage		V_{GS}	±10	V
Continuous Drain Current[1,5]	T_A = 25℃	I_D	5	A
Pulsed Drain Current[2]		I_{DM}	20	A
Power Dissipation[4,5]	T_A = 25℃	P_D	0.65	W
Thermal Resistance from Junction to Ambient[5]		$R_{\theta JA}$	190	℃/W
Junction Temperature		T_J	150	℃
Storage Temperature		T_{STG}	-55~ +150	℃

MOSFET ELECTRICAL CHARACTERISTICS (T_J = 25℃ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	20			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 18V, V_{GS} = 0V			1	μA
Gate - Body Leakage Current	I_{GSS}	V_{GS} = ±10V, V_{DS} = 0V			±100	nA
On Characteristics[3]						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	0.5	0.7	1	V
Drain-source On-resistance	$R_{DS(on)}$	V_{GS} = 4.5V, I_D = 4A	20		27	mΩ
		V_{GS} = 2.5V, I_D = 3A	23		32	
Forward Transconductance	g_{FS}	V_{DS} = 5V, I_D = 4.5A		10.5		S
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS} = 10V, V_{GS} = 0V, f = 1MHz		354		pF
Output Capacitance	C_{oss}			66		
Reverse Transfer Capacitance	C_{rss}			57		
Gate Resistance	R_g	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz		1.5		Ω
Switching Characteristics						
Total Gate Charge	Q_g	V_{DS} = 10V, V_{GS} = 4.5V, I_D = 5A		10		nC
Gate-source Charge	Q_{gs}			2.8		
Gate-drain Charge	Q_{gd}			3.0		
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 10V, V_{GS} = 4.5V, R_L = 2Ω, R_G = 3Ω		15		ns
Turn-on Rise Time	t_r			7		
Turn-off Delay Ttime	$t_{d(off)}$			35		
Turn-off Fall Time	t_f			18		
Source - Drain Diode Characteristics						
Diode Forward Voltage[3]	V_{SD}	V_{GS} = 0V, I_S = 1.25A			1.2	V

Notes :

1.The maximum current rating is limited by package.

2.Pulse Test : Pulse Width ≤ 10μs, duty cycle ≤ 1%.

3.Pulse Test : Pulse Width ≤ 300μs, duty cycle ≤ 2%.

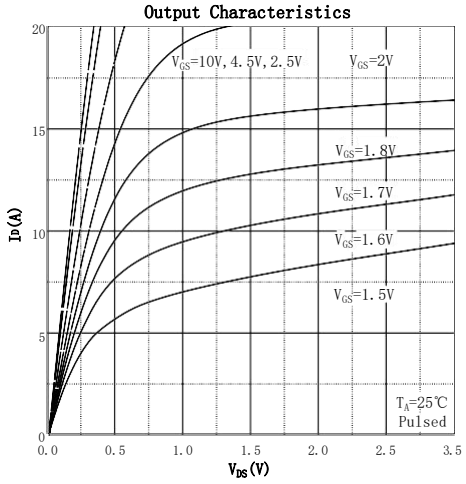
4.The power dissipation P_D is limited by $T_{J(MAX)}$ =

150°C.

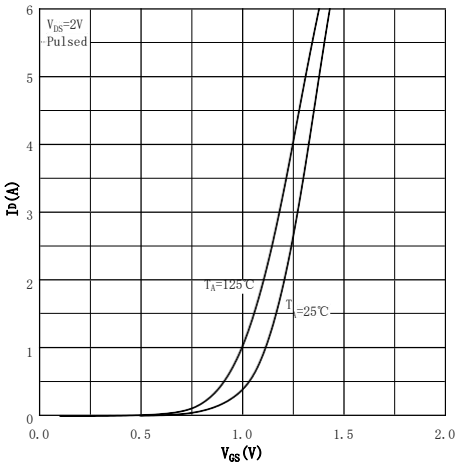
5.Device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.

Typical Characteristics

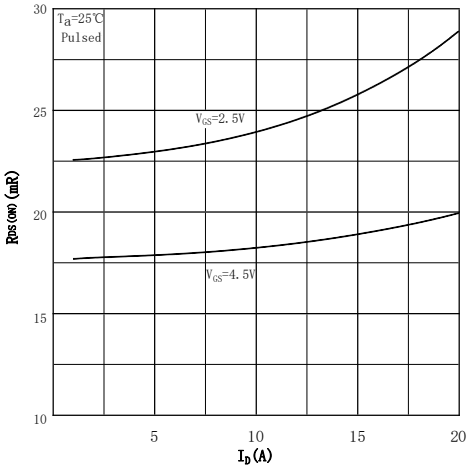
Output Characteristics



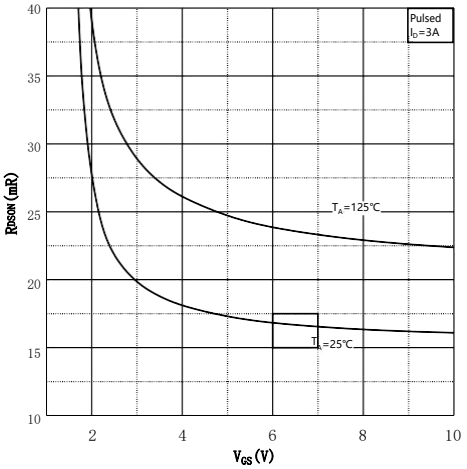
Transfer Characteristics



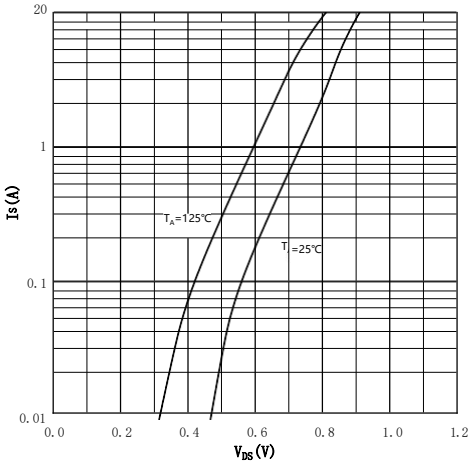
$R_{DS(ON)}$ vs I_D



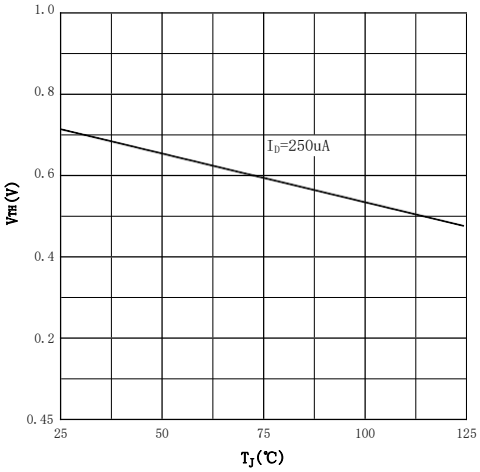
$R_{DS(ON)}$ vs V_{GS}

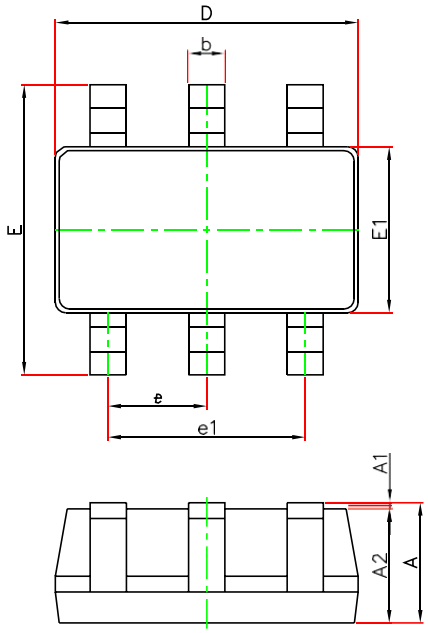


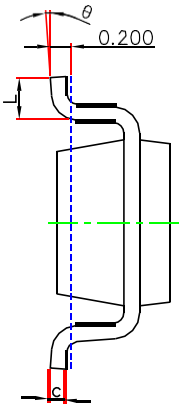
I_S vs V_{SD}



Threshold Voltage







Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°